# PL08 GaAs p-HEMT LNA



#### Features

- → 5 3000MHz
- ✤ 19.5 dB Gain at 900 MHz
- ✤ 0.79 dB Noise Figure at 900 MHz
- Single 3 V Supply Voltage
- Lead-free / Green / RoHScompliant SOT-363 Package



## Applications

- Mobile Infrastructure
- PCS, WCDMA, WiBro
- W-LAN / ISM
- RFID / Fixed Wireless

#### **Functional Diagram**



* Marking : N32				
Function	Pin No.			
RF IN	3			
RF OUT / Bias	6			
Ground	1,2,4,5			

## Description

The PL08 is a high performance GaAs p-HEMT LNA (Low Noise Amplifier) in a high quality SOT-363 package. The device features high linear performance, low noise figure, low power consumption and high reliability. The PL08 can be easily matched to obtain optimum power and linearity. The PL08 operates from a single +3 voltage supply and have an internal active bias. All devices are 100% RF and DC tested.

## **Specifications**

Symbol	Units	Freq.	Min.	Тур.	Max.
S21	dB	900 MHz 1900 MHz 2140 MHz 2600 MHz		19.5 14.5 13.5 12.0	
S11	dB	900 MHz 1900 MHz 2140 MHz 2600 MHz		-17 -18 -17 -15	
S22	dB	900 MHz 1900 MHz 2140 MHz 2600 MHz		-14 -18 -16 -18	
P1dB	dBm	900 MHz 1900 MHz 2140 MHz 2600 MHz		16.5 16.5 16.5 16.5 16.5	
OIP3	dBm	900 MHz 1900 MHz 2140 MHz 2600 MHz		30.0 33.0 33.0 33.0 33.0	
NF	dB	900 MHz 1900 MHz 2140 MHz 2600 MHz		0.79 0.92 0.96 1.15	
lcc	mA			45	
Vcc	V			3.0	
Rth	°C/W			40	

Test Conditions : T=25°C, Supply Voltage=+3V, 50ohm System, OIP3 measured with two tones at an output power of +3dBm/tone separated by 1MHz. www.prewell.com



# 800 MHz – 900 MHz Application Circuit



800 900 Frequency[MHz] S21[dB] 20.5 19.5 S11[dB] -14 -17 S22[dB] -15 -21 P1dB[dBm] +16.8 +16.8 Output IP3[dBm](1) +30.0 +30.0 NF[dB] 0.79 0.79 Vcc[V] 3 Icc[mA] 45

Note:

1. OIP3 measured with two tones at an output power of +3dBm/tone









Frequency [MHz]		900	1900	2140	2600
	-40	0.5	0.57	0.6	0.78
Temperature [°C]	25	0.79	0.92	0.96	1.15
	85	1.18	1.2	1.33	1.68



# 900 MHz – 1000 MHz Application Circuit



1000 Frequency[MHz] 900 S21[dB] 19.5 19.0 S11[dB] -19 -17 S22[dB] -14 -18 P1dB[dBm] +16.8 +16.8 Output IP3[dBm](1) +30.5 +31.0 NF[dB] 0.79 0.83 Vcc[V] 3 Icc[mA] 45

Note:

1. OIP3 measured with two tones at an output power of +3dBm/tone



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Frequency [MHz]		900	1900	2140	2600
	-40	0.5	0.57	0.6	0.78
Temperature [°C]	25	0.79	0.92	0.96	1.15
	85	1.18	1.2	1.33	1.68



# 1700 MHz – 1900 MHz Application Circuit



Note:

Distance from input blocking capacitor(100pF) to PL08 input pin: 6mm



Frequency[MHz]	1700	1900	
S21[dB]	15.5	14.5	
S11[dB]	-18	-18	
S22[dB]	-15	-18	
P1dB[dBm]	+16.8	+16.8	
Output IP3[dBm] <sup>(1)</sup>	+33.0	+33.0	
NF[dB]	0.87	0.92	
Vcc[V]	3		
lcc[mA]	45		

Note:

1. OIP3 measured with two tones at an output power of +3dBm/tone





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Frequency [MHz]		900	1900	2140	2600
	-40	0.5	0.57	0.6	0.78
Temperature [°C]	25	0.79	0.92	0.96	1.15
	85	1.18	1.2	1.33	1.68



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Frequency [MHz] 0 +25℃ -5 **-40**℃ +85℃ -10 S22 [dB] -15 -20 -25 -30 1900 1950 2000 2050 2100 2150 2200 Frequency [MHz]





Note: Distance from input blocking capacitor(100pF) to PL08 input pin: 6mm Distance from output blocking capacitor(100pF) to PL08 output pin: 6mm



Frequency[MHz]	1900	2140	
S21[dB]	14.5	13.5	
S11[dB]	-13	-17	
S22[dB]	-13	-16	
P1dB[dBm]	+16.5	+16.5	
Output IP3[dBm] <sup>(1)</sup>	+33.0	+33.5	
NF[dB]	0.92	0.96	
Vcc[V]	3		
Icc[mA]	45		

# 1900 MHz – 2200 MHz Application Circuit



Note:

0

-5

-10

-15

-20

-25

-30

1900

1950

2000

2050

Frequency [MHz]

2100

S11 [dB]

1. OIP3 measured with two tones at an output power of +3dBm/tone

+25℃

**-40**℃

+85℃

2150

2200

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Frequency [MHz]		900	1900	2140	2600
	-40	0.5	0.57	0.6	0.78
Temperature [°C]	25	0.79	0.92	0.96	1.15
	85	1.18	1.2	1.33	1.68

S21 [dB]

S22 [dB]



# 2300 MHz – 2600 MHz Application Circuit



Frequency[MHz]	2300	2600	
S21[dB]	13.0	12.0	
S11[dB]	-15	-15	
S22[dB]	-14	-18	
P1dB[dBm]	+17.0	+17.0	
Output IP3[dBm] <sup>(1)</sup>	+33.0	+33.0	
NF[dB]	1.05	1.15	
Vcc[V]	3		
Icc[mA]	45		

Note:

1. OIP3 measured with two tones at an output power of +3dBm/tone



Frequency [MHz]







Frequency [MHz]		900	1900	2140	2600
	-40	0.5	0.57	0.6	0.78
Temperature [°C]	25	0.79	0.92	0.96	1.15
	85	1.18	1.2	1.33	1.68



Parameter	Rating	Unit
Device Voltage	+6	V
Device Current	85	mA
RF Power Input	30	dBm
Storage Temperature	-55 to +125	°C
Ambient Operating Temperature	-40 to +85	°C
Junction Temperature for >10 <sup>6</sup> hours MTTF	185	°C

#### **Absolute Maximum Ratings**

Operation of this device above any of these parameters may cause permanent damage.

## ESD / MSL Ratings

- 1. ESD sensitive device. Observe Handling Precautions.
- 2. ESD Rating : Class 0(Passes at 150V max.) Human Body Model (HBM), JESD22-A114
- 3. ESD Rating : Class IV (Passes at 1000V min.) Charged Device Model (CDM), JESD22-C101
- 4. MSL (Moisture Sensitive Level) Rating : Level 1 at +260°C Convection reflow, J-STD-020

### **Evaluation Board Layout (4x4)**



## **Mounting Instructions**

- 1. Use a large ground pad area with many plated throughholes as shown.
- 2. We recommend 1 oz copper minimum.
- 3. Measurement for our data sheet was made on 0.8mm thick FR-4 Board.
- 4. Add as much copper as possible to inner and outer layers near the part to ensure optimal thermal performance.
- 5. RF trace width depends on the board material and construction.
- 6. Add mounting screws near the part to fasten the board to a heatsink.







# Lead-free / RoHS Compliant / Green SOT-363 Package Outline





)	_	Miller		Inches		
	pqu	MIIIM	elers	inc	nes	
	Syr	MIN.	MAX.	MIN.	MAX.	
	A	0.90	1.10	.036	.044	
	A1	0.025	0.10	.001	.004	
	A2	0.875	1.00	.035	.040	
	ь	0.20	0.40	.008	.016	
	С	0.10	0.15	.004	.006	
	D	1.90	2.10	.076	.084	
	Е	1.15	1.35	.046	.054	
	E1	2.00	2.20	.080	.088	
	е	0.65 BSC.		.026	BSC.	
	e1	1.30	BSC.	.052	BSC.	
	L	0.425	5 REF.	.017	REF.	

Note: 1.All dimensions are in millimeters, and the dimensions in inches are for reference only. 2.1mm=40mils=0.04inches

